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Inclosure Material:
Metal
Overall Length:
2.560 inches
Overall Diameter:
1.031 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
1.060 inches
Thread Size:
0.500 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
1000.0 off-state voltage, dc
Current Rating Per Characteristic:
150.00 milliamperes forward current, total rms preset
Power Rating Per Characteristic:
100.0 watts small-signal input power, common-collector
Maximum Operating Tempurature Per Measurement Point:
120.0 degrees celsius junction
Special Features:
Junction pattern arrangement: pnpn
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 3 uninsulated wire lead w/terminal lug
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No

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